L Number	Hits	Search Text	DB	Time stamp
-	227	438/658.ccls.	USPAT	2004/04/20 11:39
-	137	438/658.ccls. and conductive	USPAT	2003/11/18 10:36
-	136	438/658.ccls. and conductive and layer	USPAT	2003/11/18 10:37
-	68	438/658.ccls. and conductive and layer and via	USPAT	2003/11/18 10:37
-	31	438/658.ccls. and conductive and layer and via and electromigration	USPAT	2003/11/18 10:37
-	5	438/658.ccls. and conductive and layer and via and electromigration and dopant	USPAT	2003/11/18 10:37
-	1	438/658.ccls. and conductive and layer and via and electromigration and dopant and aluminum and concentrat$4 and atomic	USPAT	2003/11/18 10:38
-	2	438/658.ccls. and conductive and layer and via and electromigration and dopant and aluminum and concentrat$4	USPAT	2003/11/18 12:27
-	5	438/658.ccls. and conductive and layer and via and electromigration and dopant and aluminum	USPAT	2003/11/24 11:49
-	51	438/658.ccls. and "conductive layer"	USPAT	2003/11/21 14:11
-	50	438/658.ccls. and "conductive layer" and substrate	USPAT	2003/11/21 14:11
-	21	438/658.ccls. and "conductive layer" and substrate and "dielectric layer"	USPAT	2003/11/21 14:11
-	15	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer"	USPAT	2003/11/21 14:11
-	12	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer" and via	USPAT	2003/11/21 14:12
-	0	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer" and via and dopant	USPAT	2003/11/21 14:12
-	6	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer" and via and dop$4	USPAT	2003/11/21 14:14
-	6	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer" and via and dop$4 and electromigration	USPAT	2003/11/21 14:15
-	2	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer" and via and dop$4 and electromigration and atomic	USPAT	2003/11/21 15:19
-	0	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer" and via and dop$4 and electromigration and atomic and implant	USPAT	2003/11/21 15:19
-	2	438/658.ccls. and conductive and layer and via and electromigration and dopant and aluminum and ion	USPAT	2003/11/24 11:49
-	2	438/658.ccls. and conductive and layer and via and electromigration and dopant and aluminum and ion and gas	USPAT	2003/11/24 11:50
-	4	(("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.	USPAT	2004/04/20 11:40
-	3	((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and conduct$4 and dielectric	USPAT	2004/04/20 12:11
-	2	((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and conduct$4 and dielectric and via	USPAT	2004/04/20 12:17
-	0	((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and conduct$4 and dielectric and via and etch and ion	USPAT	2004/04/20 12:18

-	1	((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and conduct$4 and dielectric and via and etch	USPAT	2004/04/20 14:16
-	0	438/658.	USPAT	2004/04/20 14:16
-	235	438/658.ccls.	USPAT	2004/04/20 14:17
-	50	438/658.ccls. and substrate and conduct$4 and dielectric and via	USPAT	2004/04/20 14:18
-	35	438/658.ccls. and substrate and conduct$4 and dielectric and via and tin	USPAT	2004/04/20 14:29
-	23	438/658.ccls. and substrate with conduct$4 and dielectric and via and tin	USPAT	2004/04/20 15:03
-	3	438/658.ccls. and substrate with conduct$4 with barrier and dielectric and via and tin	USPAT	2004/04/29 10:18
-	0	subbstrate with conduct$4 with barrier and dielectric and via and tin	USPAT	2004/04/21 09:21
-	418	substrate with conduct$4 with barrier and dielectric and via and tin	USPAT	2004/04/21 09:43
-	2	substrate with conduct$4 with barrier and dielectric and via and tin and electronmigration	USPAT	2004/04/21 09:43
-	142	substrate with conduct$4 with barrier and dielectric and via and tin and electromigration	USPAT	2004/04/21 09:44
-	95	438/658.ccls. and conduct$4 with substrate	USPAT	2004/04/29 10:20
-	87	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide)	USPAT	2004/04/29 10:21
-	49	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide) and via	USPAT	2004/04/29 10:21
-	19	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide) and via and (dopant or impur$4)	USPAT	2004/04/29 10:21
-	10	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide) and via and (dopant or impur$4) and barrier	USPAT	2004/04/29 10:22
-	1	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide) and via and (dopant or impur$4) and barrier and ion and implant$4 and gas and trench	USPAT	2004/04/29 10:22
-	2	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide) and via and (dopant or impur$4) and barrier and ion and implant$4 and gas	USPAT	2004/04/29 10:34
-	3	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide) and via and (dopant or impur$4) and barrier and ion and implant$4	USPAT	2004/04/29 10:36
-	7	438/658.ccls. and conduct$4 with substrate and (dielectric or oxide) and via and (dopant or impur$4) and barrier and ion	USPAT	2004/04/29 10:44